

Substitute for FORM PTO-8A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

1

of

Complete If Known

Application Number	10/763,018
Filing Date	January 21, 2004
First Named Inventor	Tan, Zhengquan
Art Unit	2812
Examiner Name	Unassigned

Attorney Docket Number 016301-042210US

U.S. PATENT DOCUMENTS+

Examiner Initials*	Cite No. ¹	Document Number Number Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or 'Applicant of Cited Document'	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
MRC	AA	4,667,365	05-26-1987	Martinek	
	AB	4,690,746	09-01-1987	McInerney et al.	
	AC	4,737,379	04-12-1988	Hudgens et al.	
	AD	4,835,005	05-30-1989	Hirooka et al.	
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	AF	4,894,352	01-16-1990	Lane et al.	
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	AH	5,571,571	11-05-1996	Musaka et al.	
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	AK	5,712,185	01-27-1998	Tsai et al.	
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	AM	5,728,621	03-17-1998	Zheng et al.	
	AN	5,750,211	05-12-1998	Weise et al.	
	AO	5,804,259	09-08-1998	Robles	
	AP	5,872,058	02-16-1999	Van Cleempot et al.	
	AQ	5,872,058	02-16-1999	Van Cleempot et al.	
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	AS	5,976,327	11-02-1999	Tanaka	
	AT	5,990,013	11-23-1999	Berenguer et al.	
	AU	6,013,191	01-11-2000	Nasser-Faili et al.	
	AV	6,013,584	01-11-2000	M'Saad	
	AW	6,020,458	02-01-2000	Lee et al.	
	AX	6,030,881	02-29-2000	Papasouliotis et al.	
	AY	6,039,851	03-21-2000	Iyer	
	AZ	6,051,321	04-18-2000	Lee et al.	
	BA	6,090,167	07-18-2000	Bhan et al.	
	BB	6,149,779	11-21-2000	Van Cleempot	
	BC	6,150,212	11-21-2000	Divakaruni et al.	
	BD	6,150,285	11-21-2000	Besser et al.	
	BE	6,194,038	02-27-2001	Rossman	
	BF	6,194,038 B1	02-27-2001	Rossman	

Examiner Signature

Date Considered

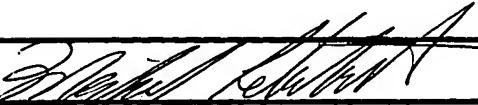
10/7/04

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Substitute for form 1449A/PTO				<i>Complete if Known</i>	
				Application Number	10/763,018
				Filing Date	January 21, 2004
				First Named Inventor	Tan, Zhengquan
				Art Unit	2812
				Examiner Name	Unassigned
Sheet	2	of		Attorney Docket Number	016301-042210US

U.S. PATENT DOCUMENTS+					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
ML	BG	6,197,691		03-06-2001	Lee
	BH	6,217,658 B1		04-17-2001	Orczyk et al.
	BI	6,228,751 B1		05-08-2001	Yamazaki et al.
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	BM	6,355,581 B1		03-12-2002	Vassiliev et al.
ML	BN	6,395,150 B1		05-28-2002	Van Cleemput et al.

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)		
ML	BO	EP	0 822 585	A2	Applied Materials	<input type="checkbox"/>
ML	BP	JP	2-58836	A	02-28-1990	<input type="checkbox"/>
ML	BQ	JP	7-161703	A	06-23-1995	<input type="checkbox"/>
ML	BR	GB	2 267 291	A	12-01-1993	<input type="checkbox"/>
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Examiner Signature		Date Considered	10/7/04
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Substitute for form 1449B/PTO				Complete If Known	
				<i>Application Number</i>	10/763,018
				<i>Filing Date</i>	January 21, 2004
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				<i>Art Unit</i>	2812
				<i>Examiner Name</i>	Unassigned
Sheet	3	of		<i>Attorney Docket Number</i>	016301-042210US

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T ²
<i>YTL</i>	BS	V.Y. Vassiliev et al., "Trends in Void Free Pre-metal CVD Dielectrics," <i>Solid State Technology</i> , pp. 129-136 (March 2001).		
	BT	L.Q. Qian et al., "High Density Plasma Deposition and Deep Submicron Gap Fill with Low Dielectric Constant SiOF Films," <i>February 21-22, 1995 DUMIC Conference</i> , pp. 50-56 (February 1995).		
	BU	T. Fukada et al., "Preparation of SiOF with Low Dielectric Constant by ECR Plasma CVD," <i>February 21-22, 1995 DUMIC Conference</i> , pp. 43-49 (February 1995).		
	BV	D. Yu et al., "Step Coverage Study of PETEOS Deposition for Intermetal Dielectric Applications," <i>June 12-13, 1990 VMIC Conference</i> , pp. 166-172 (June 1990).		
	BW	K. Musaka et al., "Single Step Gap Filling Technology for Subhalf Micron Metal Spacings on Plasma Enhanced TEOS/O ₂ Chemical Vapor Deposition System," <i>Extended Abstracts of the 1993 International Conference on Solid State Devices and Materials, Makuhari</i> , pp. 510-512 (1993).		
	BX	T. Fukuda et al., "Highly Reliable SiOF Film Formation Using High Density Plasma Containing Hydrogen," <i>February 10-11, 1997 DUMIC Conference</i> , pp. 41-49 (February 1997).		
	BY	G.Y. LEE et al., "A Low Redeposition Rate High Density Plasma CVD Process for High Aspect Ratio 175 mm Technology and Beyond," <i>Proceedings of IEEE 1999 International Interconnect Technology Conference</i> , pp. 152-154 (1999).		
	BZ	V.Y. Vassiliev et al., "Properties and Gap-Fill Capability of HDP-CVD Phosphosilicate Glass Films for Subquarter-Micrometer ULSI Device Technology," <i>Electrochemical and Solid-State Letters</i> , vol. 3, no. 2, pp. 80-83 (2000).		
	CA	NALWA, H.S., <i>Handbook of Low and High Dielectric Constant Materials and Their Applications</i> , vol. 1, page 66 (1999).		
<i>YTL</i>	CB	NGUYEN, s.v., "High-Density Plasma Chemical Vapor Deposition of Silicon-Based Dielectric Films for Integrated Circuits," <i>Journal of Research and Development</i> , vol. 43, 1/2 (1999).		

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